

[illegible]

A cross-sectional view of a semiconductor device. A central channel region 11 is shown with vertical hatching. It is flanked by source/drain regions 12 and 13, which are filled with a diagonal hatching pattern. Above the channel, a gate stack 15 is formed, with a gate electrode 14 on top. The device is on a substrate 10. A window W is defined in the substrate. A dashed line indicates a profile PL. Labels 10, 11, 12, 13, 14, 15, and W are used to identify the various components.